

TCAD simulations of p-bulk silicon sensors after a large range of fluences

Tuesday 22 November 2016 16:10 (20 minutes)

In this talk I will present recent results from TCAD simulations using Silvaco tools.

In particular I will focus on p-bulk sensors, both standard diodes and LGADs.

At the beginning I will present a comparison of two radiation damage models for the bulk (Perugia, New Delhi).

Then I will comment on the impact of radiation damage model parameters uncertainties on macroscopic observables.

Eventually I will present some results on simulated thin LGADs under laser red light illumination.

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